
HZ Series

Silicon Epitaxial Planar Zener Diode for Stabilized Power Supply

HITACHI

ADE-208-117B(Z)

Rev. 2
Nov. 1999

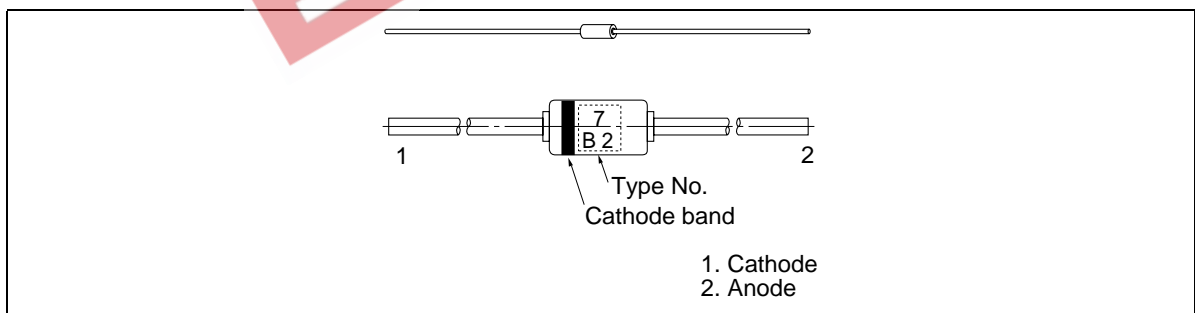
Features

- Low leakage, low zener impedance and maximum power dissipation of 500 mW are ideally suited for stabilized power supply, etc.
- Wide spectrum from 1.6V through 38V of zener voltage provide flexible application.

Ordering Information

Type No.	Mark	Package Code
HZ Series	Type No.	DO-35

Outline



HZ Series

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd	500	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-55 to +175	°C

Electrical Characteristics

(Ta = 25°C)

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		V _z (V)* ¹		Test Condition	Test Condition	r _d (Ω)	Test Condition	
		Min	Max	I _z (mA)	I _R (μA) Max	V _R (V)	I _z (mA)	
HZ2	A1	1.6	1.8	5	25	0.5	100	5
	A2	1.7	1.9					
	A3	1.8	2.0					
	B1	1.9	2.1	5	5	0.5	100	5
	B2	2.0	2.2					
	B3	2.1	2.3					
	C1	2.2	2.4					
	C2	2.3	2.5					
	C3	2.4	2.6					
HZ3	A1	2.5	2.7	5	5	0.5	100	5
	A2	2.6	2.8					
	A3	2.7	2.9					
	B1	2.8	3.0					
	B2	2.9	3.1					
	B3	3.0	3.2					
	C1	3.1	3.3					
	C2	3.2	3.4					
	C3	3.3	3.5					
HZ4	A1	3.4	3.6	5	5	1.0	100	5
	A2	3.5	3.7					
	A3	3.6	3.8					

Note: 1. Tested with DC.

HZ Series

Type	Grade	Zener Voltage		Test Condition I_z (mA)	Reverse Current		Dynamic Resistance	
		V_z (V)* ¹			I_R (μ A)	Test Condition	r_d (Ω)	Test Condition
		Min	Max		Max	V_R (V)	Max	I_z (mA)
HZ4	B1	3.7	3.9	5	5	1.0	100	5
	B2	3.8	4.0					
	B3	3.9	4.1					
	C1	4.0	4.2					
	C2	4.1	4.3					
	C3	4.2	4.4					
HZ5	A1	4.3	4.5	5	5	1.5	100	5
	A2	4.4	4.6					
	A3	4.5	4.7					
	B1	4.6	4.8					
	B2	4.7	4.9					
	B3	4.8	5.0					
	C1	4.9	5.1					
	C2	5.0	5.2					
	C3	5.1	5.3					
HZ6	A1	5.2	5.5	5	5	2.0	40	5
	A2	5.3	5.6					
	A3	5.4	5.7					
	B1	5.5	5.8					
	B2	5.6	5.9					
	B3	5.7	6.0					
	C1	5.8	6.1					
	C2	6.0	6.3					
	C3	6.1	6.4					
HZ7	A1	6.3	6.6	5	1	3.5	15	5
	A2	6.4	6.7					
	A3	6.6	6.9					
	B1	6.7	7.0					
	B2	6.9	7.2					
	B3	7.0	7.3					

Note: 1. Tested with DC.

HZ Series

Type	Grade	Zener Voltage		Test Condition I_z (mA)	Reverse Current		Dynamic Resistance	
		V_z (V)* ¹			I_R (μ A)	Test Condition	r_d (Ω)	Test Condition
		Min	Max		Max	V_R (V)	Max	I_z (mA)
HZ7	C1	7.2	7.6	5	1	3.5	15	5
	C2	7.3	7.7					
	C3	7.5	7.9					
HZ9	A1	7.7	8.1	5	1	5.0	20	5
	A2	7.9	8.3					
	A3	8.1	8.5					
	B1	8.3	8.7					
	B2	8.5	8.9					
	B3	8.7	9.1					
	C1	8.9	9.3					
	C2	9.1	9.5					
	C3	9.3	9.7					
HZ11	A1	9.5	9.9	5	1	7.5	25	5
	A2	9.7	10.1					
	A3	9.9	10.3					
	B1	10.2	10.6					
	B2	10.4	10.8					
	B3	10.7	11.1					
	C1	10.9	11.3					
	C2	11.1	11.6					
	C3	11.4	11.9					
HZ12	A1	11.6	12.1	5	1	9.5	35	5
	A2	11.9	12.4					
	A3	12.2	12.7					
	B1	12.4	12.9					
	B2	12.6	13.1					
	B3	12.9	13.4					
	C1	13.2	13.7					
	C2	13.5	14.0					
	C3	13.8	14.3					

Note: 1. Tested with DC.

HZ Series

Type	Grade	Zener Voltage		Test Condition I_z (mA)	Reverse Current		Dynamic Resistance	
		V_z (V)* ¹			I_R (μ A)	Test Condition	r_d (Ω)	Test Condition
		Min	Max		Max	V_R (V)	Max	I_z (mA)
HZ15	1	14.1	14.7	5	1	11.0	40	5
	2	14.5	15.1					
	3	14.9	15.5					
HZ16	1	15.3	15.9	5	1	12.0	45	5
	2	15.7	16.5					
	3	16.3	17.1					
HZ18	1	16.9	17.7	5	1	13.0	55	5
	2	17.5	18.3					
	3	18.1	19.0					
HZ20	1	18.8	19.7	2	1	15.0	60	2
	2	19.5	20.4					
	3	20.2	21.1					
HZ22	1	20.9	21.9	2	1	17.0	65	2
	2	21.6	22.6					
	3	22.3	23.3					
HZ24	1	22.9	24.0	2	1	19.0	70	2
	2	23.6	24.7					
	3	24.3	25.5					
HZ27	1	25.2	26.6	2	1	21.0	80	2
	2	26.2	27.6					
	3	27.2	28.6					
HZ30	1	28.2	29.6	2	1	23.0	100	2
	2	29.2	30.6					
	3	30.2	31.6					
HZ33	1	31.2	32.6	2	1	25.0	120	2
	2	32.2	33.6					
	3	33.2	34.6					
HZ36	1	34.2	35.7	2	1	27.0	140	2
	2	35.3	36.8					
	3	36.4	38.0					

Note: 1. Tested with DC.

Note: 2. Type No. is as follows; HZ2B1, HZ2B2, HZ36-3.

HZ Series

Main Characteristic



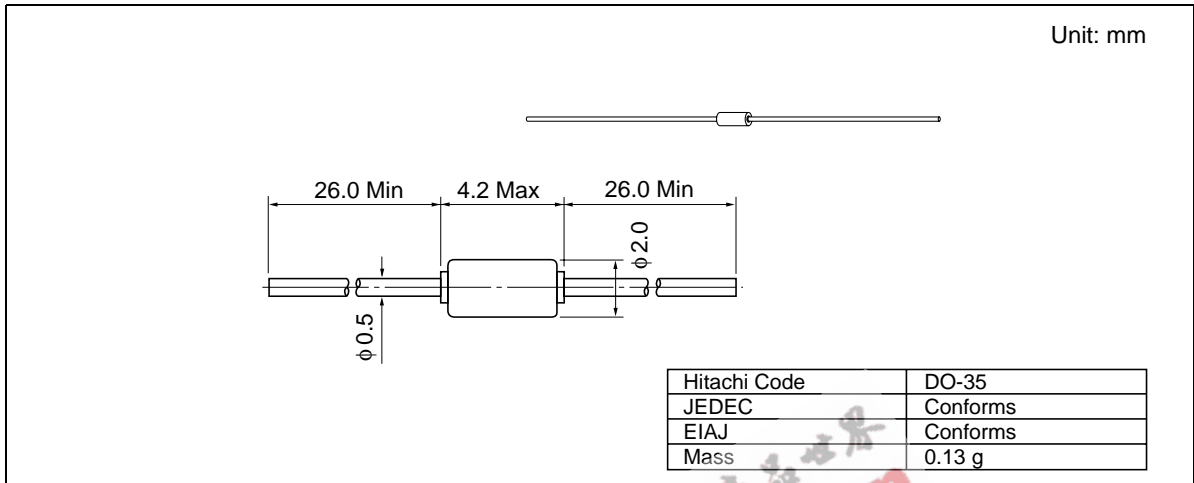
Fig.1 Zener current Vs. Zener voltage



Fig.2 Temperature Coefficient Vs. Zener voltage



Fig.3 Power Dissipation Vs. Ambient Temperature

Package Dimensions

EEPW.com.cn 电子产品世界

HZ Series

Disclaimer

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

Sales Offices

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL	North America	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe Ltd.
Electronic Components Group
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585200

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://semiconductor.hitachi.com.hk>

Copyright © Hitachi, Ltd., 2001. All rights reserved. Printed in Japan.
Colophon 4.0